

BRD4N50F

Rev.A Apr.-2024

TO-252 N MOS

N-CHANNEL MOSFET in a TO-252 Plastic Package.

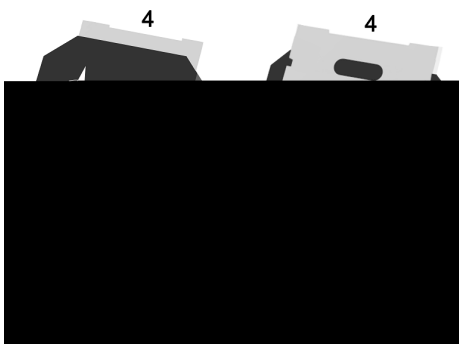
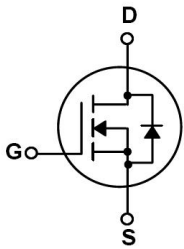
$V_{DS}=500V$ $I_D=4A$

$R_{DS(ON)}@10V$ 2.2 (Typ. 1.7)

Fast Switching.

HF Product.

These devices are well suited for power switch circuit of adaptor and charger, intergrate fast recovery diode.



PIN1 G

PIN 2 D

PIN 3 S

PIN 4 D

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	500	V
Drain Current	$I_D(T_C=25)$	4	A
Drain Current - Pulsed	I_{DM}	8	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	176.4	mJ
Avalanche Current	I_{AS}	6.3	A
Power Dissipation	$P_D(T_C=25)$	50	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	
Junction to Ambient	R_{JA}	110	/W
Junction to Case	R_{JC}	2.5	/W

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250$ A	500			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=500V$ $V_{GS}=0V$			1	A
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250$ A	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=2.0A$		1.7	2.2	
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0$ V $I_S=1.0A$			1.4	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		350		pF
Output Capacitance	C_{oss}			145		
Reverse Transfer Capacitance	C_{rss}			5		
Total Gate Charge	Q_G	$V_{DS}=400V$ $I_D=4.0A$ $V_{GS}=10V$		8.5		nC
Gate-Source Charge	Q_{GS}			3.2		
Gate-Drain Charge	Q_{GD}			1.5		

/ Electrical Characteristics(Ta=25)

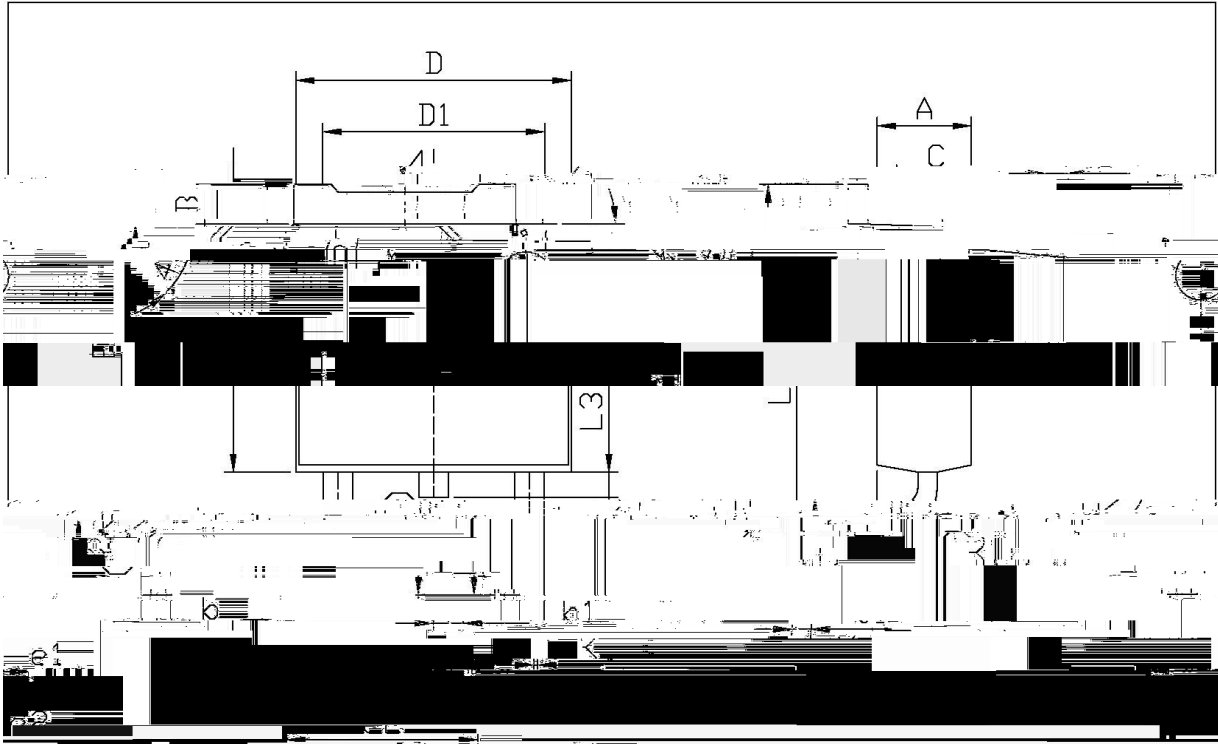
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=100V$ $I_D=4.0A$ $V_{GS}=10V$ $R_G=25$		4.3		ns
Turn-On Rise Time	t_r			17.2		
Turn-Off Delay Time	$t_{d(off)}$			22		
Turn-Off Fall Time	t_f			23.2		
Maximum Continuous Drain-Source Diode Forward Current	I_S				4	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				8	A
Reverse Recovery Time	t_{rr}	$V_{GS}=0V$ $I_S=5.0A$ $dI_F/dt=100 A/s$		92		ns
Reverse Recovery Charge	Q_{rr}			1.45		μC

BRD4N50F

Rev.A Apr.-2024



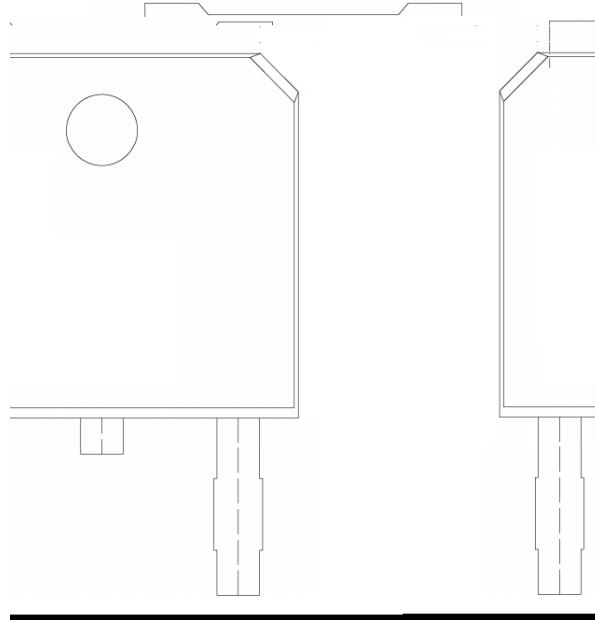
/ Package Dimensions



单位: mm

Dimensions, Millimeters		Dimensions, In Millimeters	
Min	Max	Min	Max
34.00	34.00	1.34	1.34
6.75	6.75	0.27	0.27
0.95	0.95	0.04	0.04
1.25	1.25	0.05	0.05
e1	e1	0.02	0.02
2.24	2.24	0.09	0.09
2.24	2.24	0.09	0.09
0.70	0.70	0.03	0.03
0.90	0.90	0.04	0.04
4.73	4.73	0.19	0.19
0.15	0.15	0.006	0.006
0.55	0.55	0.022	0.022
0.60	0.60	0.024	0.024
0.005	0.005	0.0002	0.0002
5.10	5.10	0.20	0.20
5.50	5.50	0.22	0.22
0.00	0.00	0.00	0.00
0.10	0.10	0.004	0.004
0.1	0.1	0.004	0.004

TO-252



BRD4N50F
Rev.A Apr.-2024